

150 V, 2 A PNP high-voltage low VCEsat transistor

17 July 2023

Product data sheet

### 1. General description

PNP high-voltage low  $V_{CEsat}$  transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8215Z-Q

## 2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  $I_C$  and  $I_{CM}$
- High collector current gain  $h_{FE}$  at high  $I_C$
- Medium power SMD plastic package
- Qualified according to AEC-Q101 and recommended for use in automotive applications

### 3. Applications

- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Switch Mode Power Supply (SMPS)

## 4. Quick reference data

| Table 1. Quick reference data |                              |   |  |     |     |      |      |
|-------------------------------|------------------------------|---|--|-----|-----|------|------|
| Symbol                        | Parameter                    | Conditions  |  | Min | Тур | Max  | Unit |
| V <sub>CEO</sub>              | collector-emitter<br>voltage | open base   |  | -   | -   | -150 | V    |
| I <sub>C</sub>                | collector current            |   |  | -   | -   | -2   | А    |
| h <sub>FE</sub>               | DC current gain              | $V_{CE}$ = -10 V; I <sub>C</sub> = -100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ = 0.02; T <sub>amb</sub> = 25 °C |  | 100 | 180 | -    |      |

## 5. Pinning information

| Table 2 | 2. Pinning info | ormation    |                    |                |
|---------|-----------------|-------------|--------------------|----------------|
| Pin     | Symbol          | Description | Simplified outline | Graphic symbol |
| 1       | В               | base        | 4                  | C              |
| 2       | С               | collector   |                    | в              |
| 3       | E               | emitter     |                    |                |
| 4       | С               | collector   |                    | Ė              |
|         |                 |             | SC-73 (SOT223)     | sym028         |



### 6. Ordering information

| Table 3. Ordering information |         |  |               |  |  |  |
|-------------------------------|---------|--|---------------|--|--|--|
| Type number                   | Package |  |               |  |  |  |
|                               | Name    | Description  | Version       |  |  |  |
| PBHV9215Z-Q                   | SC-73   | plastic, surface-mounted package with increased heatsink;<br>4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body | <u>SOT223</u> |  |  |  |

### 7. Marking

| Table 4. Marking codes |              |  |  |  |
|------------------------|--------------|--|--|--|
| Type number            | Marking code |  |  |  |
| PBHV9215Z-Q            | V9215Z       |  |  |  |

### 8. Limiting values

#### Table 5. Limiting values

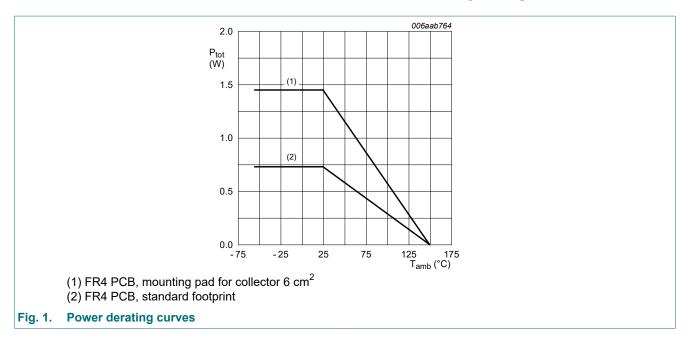
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                 | Conditions                          |     | Min | Max  | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|------|------|
| V <sub>CBO</sub> | collector-base voltage    | open emitter                        |     | -   | -200 | V    |
| V <sub>CEO</sub> | collector-emitter voltage | open base                           |     | -   | -150 | V    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector                      |     | -   | -6   | V    |
| I <sub>C</sub>   | collector current         |                                     |     | -   | -2   | А    |
| I <sub>CM</sub>  | peak collector current    | single pulse; t <sub>p</sub> ≤ 1 ms |     | -   | -4   | А    |
| I <sub>BM</sub>  | peak base current         |                                     |     | -   | -500 | mA   |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 0.73 | W    |
|                  |                           |                                     | [2] | -   | 1.45 | W    |
| Tj               | junction temperature      |                                     |     | -   | 150  | °C   |
| T <sub>amb</sub> | ambient temperature       |                                     |     | -55 | 150  | °C   |
| T <sub>stg</sub> | storage temperature       |                                     |     | -65 | 150  | °C   |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

#### 150 V, 2 A PNP high-voltage low VCEsat transistor

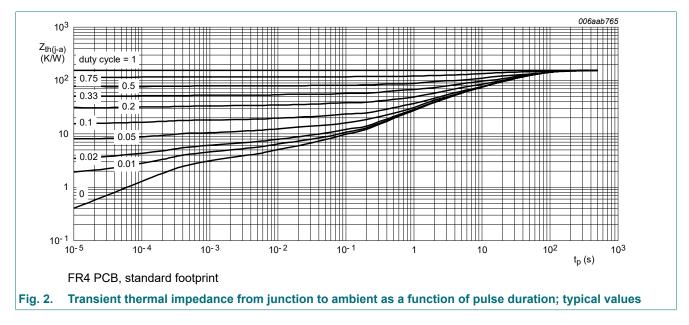


### 9. Thermal characteristics

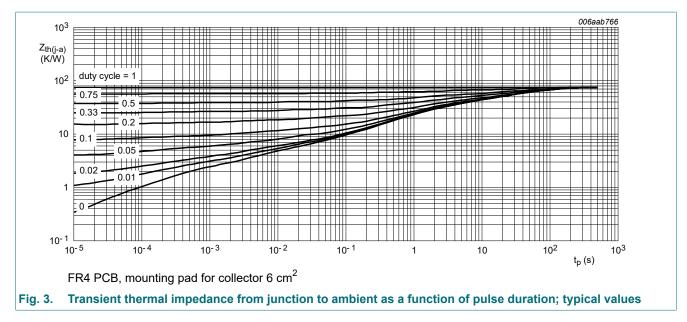
| Symbol                | Parameter  | Conditions |     | Min | Тур | Мах | Unit |
|-----------------------|--|------------|-----|-----|-----|-----|------|
| un(-α)                |  | [1]        | -   | -   | 170 | K/W |      |
|                       | junction to ambient                              |            | [2] | -   | -   | 85  | K/W  |
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point |            |     | -   | -   | 15  | K/W  |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



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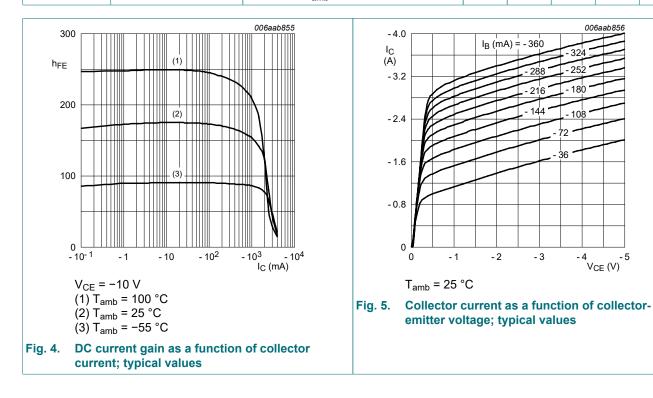


### **10. Characteristics**

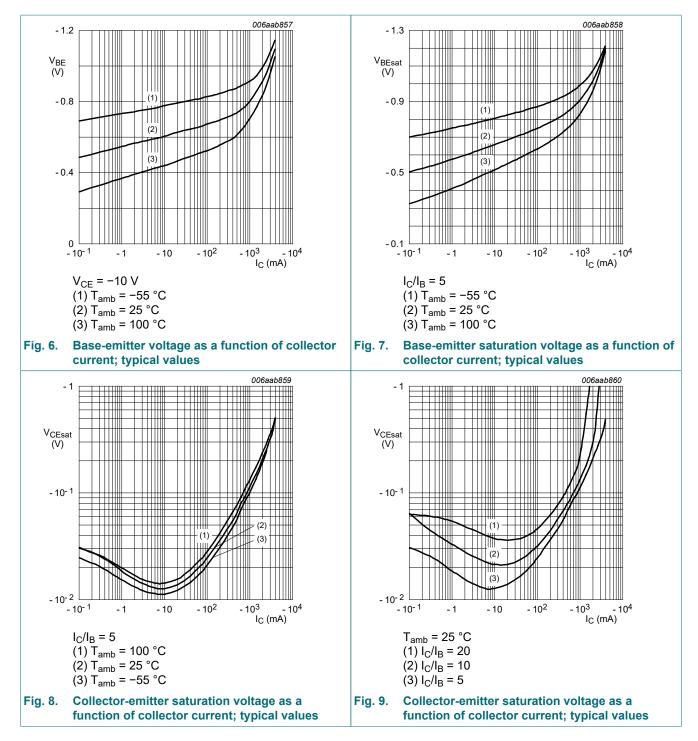
| Symbol                          | Parameter  | Conditions  | Min  | Тур  | Max   | Unit |  |
|---------------------------------|--|---|--|------|-------|------|--|
| I <sub>CBO</sub>                | collector-base cut-off   | V <sub>CB</sub> = -120 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C                      | -  | -    | -100  | nA   |  |
|                                 | current  | V <sub>CB</sub> = -120 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C                       | -  | -    | -10   | μA   |  |
| I <sub>EBO</sub>                | emitter-base cut-off current   | V <sub>EB</sub> = -4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C                        | -  | -    | -100  | nA   |  |
| I <sub>CES</sub>                | collector-emitter cut-off<br>current   | V <sub>CE</sub> = -120 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C                     | -  | -    | -100  | nA   |  |
| h <sub>FE</sub> DC current gain | $V_{CE}$ = -10 V; I <sub>C</sub> = -100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ = 0.02; T <sub>amb</sub> = 25 °C        | 100   | 180  | -    |       |      |  |
|                                 | V <sub>CE</sub> = -10 V; I <sub>C</sub> = -1 A; pulsed; t <sub>p</sub> ≤<br>300 μs; δ = 0.02; T <sub>amb</sub> = 25 °C | 80  | 155  | -    |       |      |  |
|                                 |  |   | $V_{CE}$ = -10 V; I <sub>C</sub> = -1.5 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ = 0.02; T <sub>amb</sub> = 25 °C | 70   | 140   | -    |  |
|                                 | $V_{CE}$ = -10 V; I <sub>C</sub> = -2 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ = 0.02; T <sub>amb</sub> = 25 °C           | 60  | 120  | -    |       |      |  |
| V <sub>CEsat</sub>              | collector-emitter<br>saturation voltage  | $I_{C}$ = -100 mA; $I_{B}$ = -20 mA; pulsed; $t_{p} \le$ 300 μs; δ = 0.02; $T_{amb}$ = 25 °C  | -  | -25  | -50   | mV   |  |
|                                 |  | $I_{C}$ = -1 A; $I_{B}$ = -200 mA; pulsed; $t_{p} \le$<br>300 μs; δ = 0.02; $T_{amb}$ = 25 °C | -  | -110 | -190  | mV   |  |
|                                 |  | $I_C$ = -1.5 A; $I_B$ = -300 mA; pulsed; $t_p$ ≤ 300 μs; δ = 0.02; $T_{amb}$ = 25 °C          | -  | -155 | -270  | mV   |  |
|                                 |  | $I_{C}$ = -2 A; $I_{B}$ = -400 mA; pulsed; $t_{p} \le$ 300 μs; δ = 0.02; $T_{amb}$ = 25 °C    | -  | -200 | -350  | mV   |  |
| R <sub>CEsat</sub>              | collector-emitter saturation resistance  | $I_{C}$ = -2 A; $I_{B}$ = -400 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C    | -  | 100  | 175   | mΩ   |  |
| V <sub>BEsat</sub>              | base-emitter saturation voltage  |   | -  | -1   | -1.15 | V    |  |

#### Table 7. Characteristics

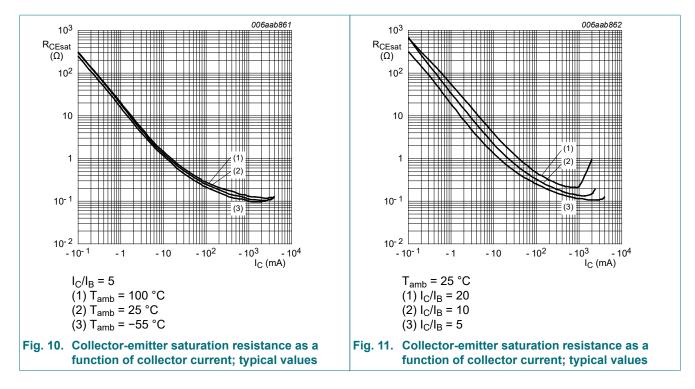
| Symbol           | Parameter             | Conditions   | Min | Тур  | Мах | Unit |
|------------------|-----------------------|--|-----|------|-----|------|
| t <sub>d</sub>   | delay time            | V <sub>CC</sub> = -6 V; I <sub>C</sub> = -0.5 A; I <sub>Bon</sub> = -0.1 A;                                  | -   | 20   | -   | ns   |
| t <sub>r</sub>   | rise time             | I <sub>Boff</sub> = 0.1 A; T <sub>amb</sub> = 25 °C  | -   | 105  | -   | ns   |
| t <sub>on</sub>  | turn-on time          |  | -   | 125  | -   | ns   |
| t <sub>s</sub>   | storage time          | _  | -   | 875  | -   | ns   |
| t <sub>f</sub>   | fall time             |  | -   | 150  | -   | ns   |
| t <sub>off</sub> | turn-off time         |  | -   | 1025 | -   | ns   |
| f <sub>T</sub>   | transition frequency  | $V_{CE}$ = -10 V; I <sub>C</sub> = -10 mA; f = 100 MHz;<br>T <sub>amb</sub> = 25 °C                          | -   | 35   | -   | MHz  |
| C <sub>c</sub>   | collector capacitance | V <sub>CB</sub> = -20 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A;<br>f = 1 MHz; T <sub>amb</sub> = 25 °C  | -   | 30   | -   | pF   |
| C <sub>e</sub>   | emitter capacitance   | V <sub>EB</sub> = -0.5 V; I <sub>C</sub> = 0 A; i <sub>c</sub> = 0 A;<br>f = 1 MHz; T <sub>amb</sub> = 25 °C | -   | 530  | -   | pF   |



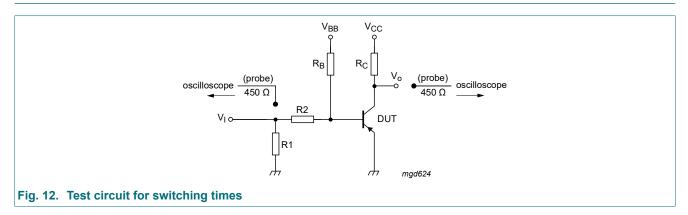
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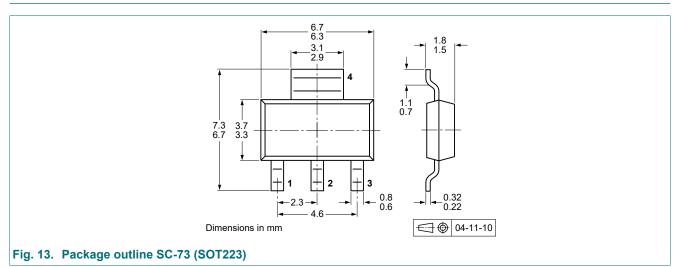
### 11. Test information



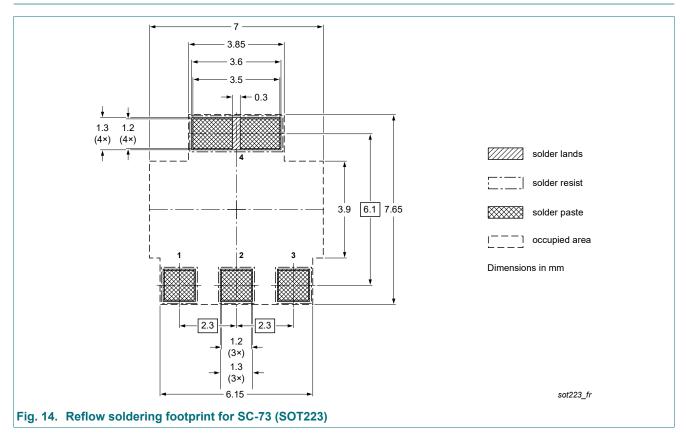
#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

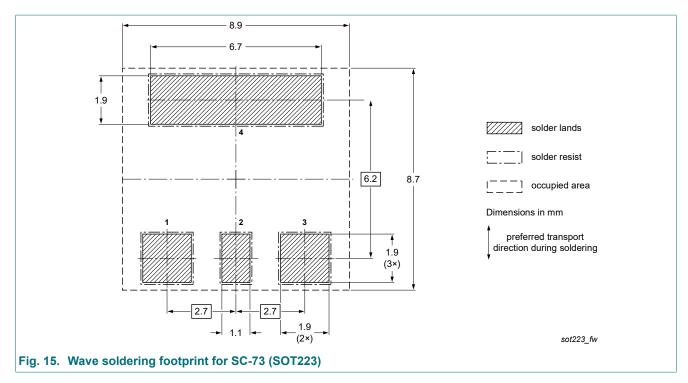
## 12. Package outline



### 13. Soldering



#### 150 V, 2 A PNP high-voltage low VCEsat transistor



## 14. Revision history

| Table 8. Revision history |              |                    |               |            |  |
|---------------------------|--------------|--------------------|---------------|------------|--|
| Data sheet ID             | Release date | Data sheet status  | Change notice | Supersedes |  |
| PBHV9215Z-Q v.1           | 20230717     | Product data sheet | -             | -          |  |

## 15. Legal information

#### **Data sheet status**

| Document status<br>[1][2]         | Product<br>status [3] | Definition  |
|-----------------------------------|-----------------------|---|
| Objective [short]<br>data sheet   | Development           | This document contains data from<br>the objective specification for<br>product development. |
| Preliminary [short]<br>data sheet | Qualification         | This document contains data from the preliminary specification.                             |
| Product [short]<br>data sheet     | Production            | This document contains the product specification.   |

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